

**MNLM3940-3.3-X REV 0B0**

 Original Creation Date: 09/30/97  
 Last Update Date: 11/18/98  
 Last Major Revision Date: 09/30/97

## 1A LOW DROPOUT REGULATOR

### General Description

The LM3940 is a 1A low dropout regulator designed to provide 3.3V from a 5V supply.

The LM3940 is ideally suited for systems which contain both 5V and 3.3V logic, with prime power provided from a 5V bus.

Because the LM3940 is a true low dropout regulator, it can hold its 3.3V output in regulation with input voltages as low as 4.5V.

### Industry Part Number

LM3940

### NS Part Numbers

 LM3940J-3.3-QML\*  
 LM3940WG3.3-QML\*\*

### Prime Die

LM3940

### Controlling Document

5962-9688401QEA\*, QXA\*\*

### Processing

MIL-STD-883, Method 5004

### Quality Conformance Inspection

MIL-STD-883, Method 5005

Subgrp	Description	Temp ( °C)
1	Static tests at	+25
2	Static tests at	+125
3	Static tests at	-55
4	Dynamic tests at	+25
5	Dynamic tests at	+125
6	Dynamic tests at	-55
7	Functional tests at	+25
8A	Functional tests at	+125
8B	Functional tests at	-55
9	Switching tests at	+25
10	Switching tests at	+125
11	Switching tests at	-55

**Features**

- Excellent load regulation
- Guaranteed 1A output current
- Requires only one external component
- Built-in protection against excess temperature
- Short circuit protected

**Applications**

- Logic Systems

**(Absolute Maximum Ratings)**

(Note 1)

Input Supply Voltage	7.5V
Internal Power Dissipation (Note 2, 3)	Internally Limited
Operating Ambient Temperature	-55 C to +125 C
Storage Temperature Range	-65 C to +150 C
Maximum Junction Temperature	150 C
Thermal Resistance (Note 3)	
ThetaJA	
CERDIP	(Still Air) 74 C/W
	(500LF/Min Air flow) 37 C/W
CERAMIC SOIC	(Still Air) 122 C/W
	(500LF/Min Air flow) 77 C/W
ThetaJC	
CERDIP	4 C/W
CERAMIC SOIC	5 C/W
Package Weight	
CEDIP	1970mg
CERAMIC SOIC	360mg
Lead Temperature (Soldering, 5 seconds)	260 C
ESD Susceptibility (Note 4)	4kV

Note 1: Absolute Maximum Ratings are limits beyond which damage to the device may occur. Operating Ratings are conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions see the Electrical Characteristics. The guaranteed specification apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 2: The maximum power dissipation must be derated at elevated temperatures and is dictated by Tjmax (maximum junction temperature), ThetaJA (package junction to ambient thermal resistance), and TA (ambient temperature). The maximum allowable power dissipation at any temperature is  $P_{dmax} = (T_{jmax} - T_A) / \Theta_{JA}$  or the number given in the Absolute Maximum Ratings, whichever is lower.

Note 3: The package material for these devices allows much improved heat transfer over our standard ceramic packages. In order to take full advantage of this improved heat transfer, heat sinking must be provided between the package base (directly beneath the die), and either metal traces on, or thermal vias through, the printed circuit board. Without this additional heat sinking, device power dissipation must be calculated using junction-to-ambient, rather than junction-to-case, thermal resistance. It must not be assumed that the device leads will provide substantial heat transfer out of the package, since the thermal resistance of the leadframe material is very poor, relative to the material of the package base. The stated junction-to-case thermal resistance is for the package material only, and does not account for the additional thermal resistance between the package base and the printed circuit board. The user must determine the value of the additional thermal resistance and must combine this with the stated value for the package, to calculate the total allowed power dissipation for the device.

Note 4: Human body model, 100pF discharged through 1.5K Ohms

## Electrical Characteristics

### DC PARAMETERS:

(The following conditions apply to all the following parameters, unless otherwise specified.)  
 DC:  $V_{in} = 5V$ ,  $I_L = 1A$ ,  $C_{out} = 33\mu F$

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN-NAME	MIN	MAX	UNIT	SUB-GROUPS
Vout	Output Voltage	$5mA \leq I_L \leq 1A$			3.20	3.40	V	1
		$5mA \leq I_L \leq 1A$			3.13	3.47	V	2, 3
Delta Vo/Delta Vi	Line Regulation	$I_L = 5mA, 4.5V \leq V_{in} \leq 5.5V$				40	mV	1
		$I_L = 5mA, 4.5V \leq V_{in} \leq 5.5V$				99	mV	2, 3
Delta Vo/IL	Load Regulation	$50mA \leq I_L \leq 1A$				50	mV	1
		$50mA \leq I_L \leq 1A$				80	mV	2, 3
Iq	Quiescent Current	$4.5V \leq V_{in} \leq 5.5V, I_L = 5mA$				15	mA	1
		$4.5V \leq V_{in} \leq 5.5V, I_L = 5mA$				20	mA	2, 3
		$V_{in} = 5V, I_L = 1A$				200	mA	1
						250	mA	2, 3
Vo - Vin	Dropout Voltage	$I_L = 1A$	1			0.8	V	1
			1			1.0	V	2, 3
		$I_L = 100mA$	1			150	mV	1
			1			200	mV	2, 3
IL(SC)	Short Circuit Current	$R_L = 0$			1.2		A	1, 2, 3

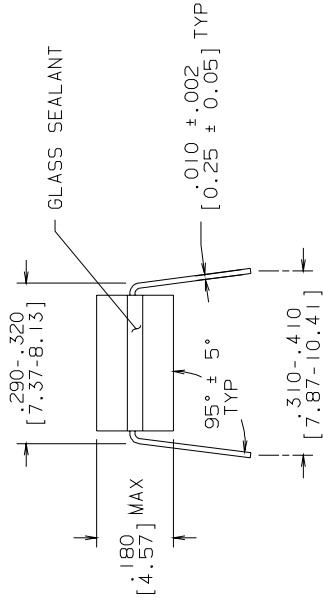
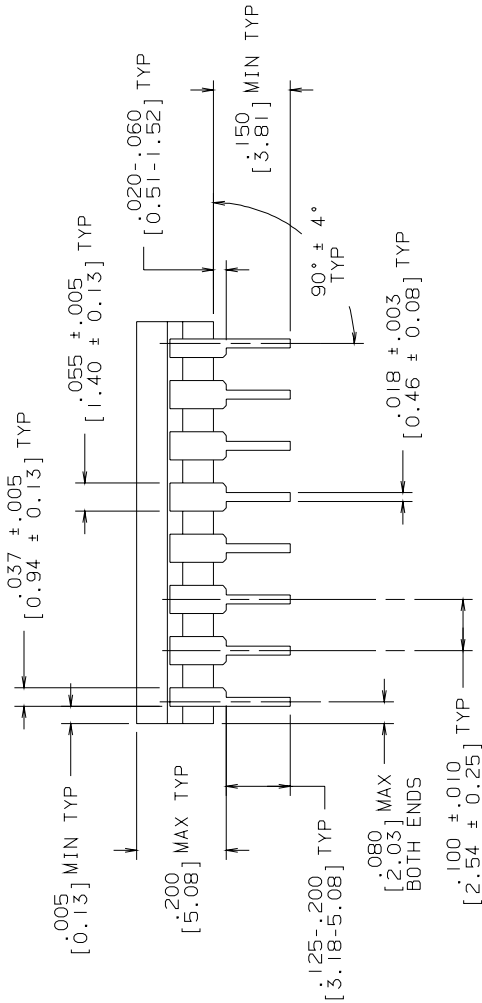
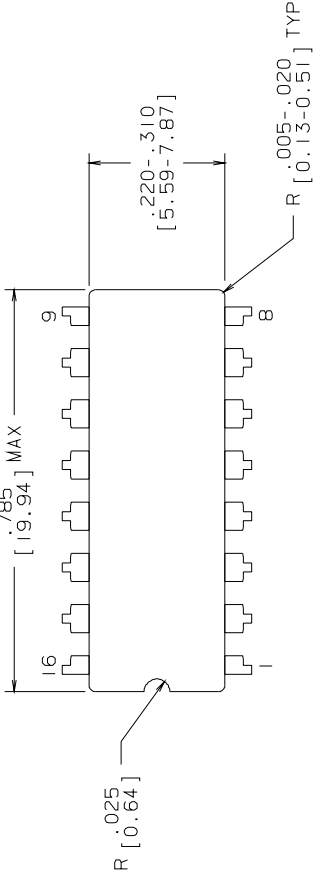
Note 1: Dropout voltage is defined as the input-output differential voltage where the regulator output drops to a value that is 100 mV below the value that is measured at  $V_{in} = 5V$ .

## Graphics and Diagrams

GRAPHICS#	DESCRIPTION
06332HRA2	CERDIP (J), 16 LEAD (B/I CKT)
06351HRA1	CERPACK (W), 16 LEAD (B/I CKT)
J16ARL	CERDIP (J), 16 LEAD (P/P DWG)
P000377A	CERAMIC SOIC (WG), 16 LEAD (PINOUT)
P000389A	CERDIP (J), 16 LEAD (PINOUT)
WG16ARC	CERAMIC SOIC (WG), 16 LEAD (P/P DWG)

See attached graphics following this page.

R E V I S I O N S				
LTR	DESCRIPTION	E.C.N.	DATE	BY/APP'D
L	REVISE PER CURRENT STD; REDRAW	09996	09/15/93	TL/



MIL/AERO  
CONFIGURATION CONTROL

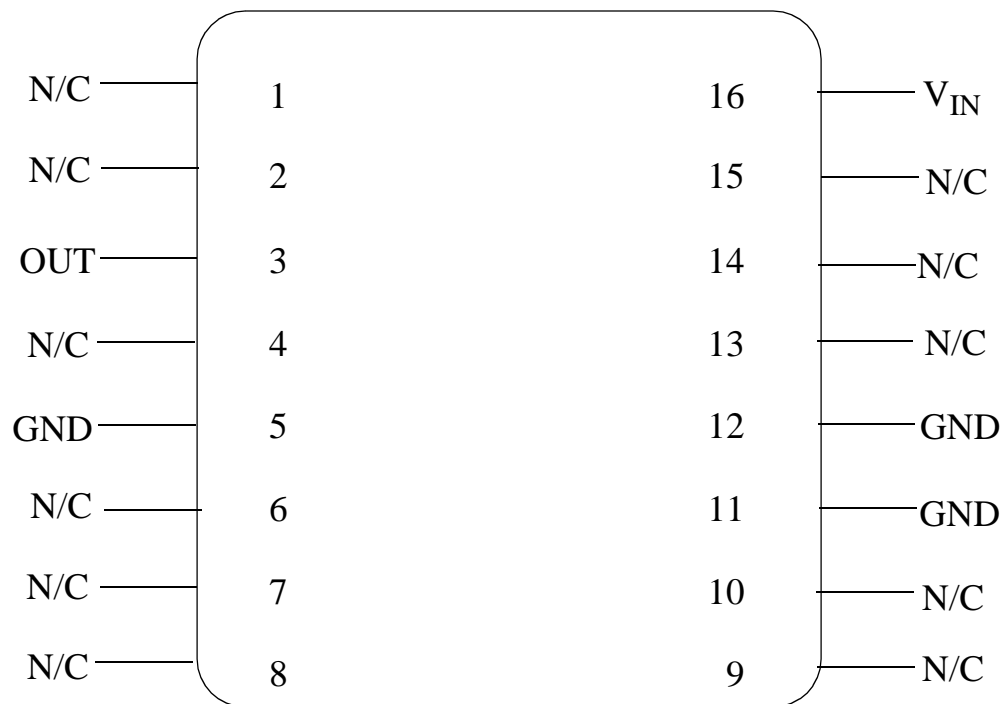
MIL-M-38510  
CONFIGURATION CONTROL

CONTROLLING DIMENSION: INCH				
APPROVALS	DATE	NATIONAL SEMICONDUCTOR CORPORATION		
DRAWN <b>LEQUANG</b>	09/15/93	2900 Semiconductor Drive, Santa Clara, CA 95052-8090		
DFTG. CHK.				
ENGR. CHK.				
APPROVAL				
PROJECTION 		SCALE N/A	SIZE B	DRAWING NUMBER MKT-J16A
		DO NOT SCALE	DRAWING	SHEET 1 OF 1

NOTES: UNLESS OTHERWISE SPECIFIED

1. LEAD FINISH TO BE 200 MICRONS / 5.08 MICROMETERS MINIMUM SOLDER MEASURED AT THE CREST OF THE MAJOR FLATS.
2. JEDEC REGISTRATION M0-036, VARIATION AD, DATED 04/1981.

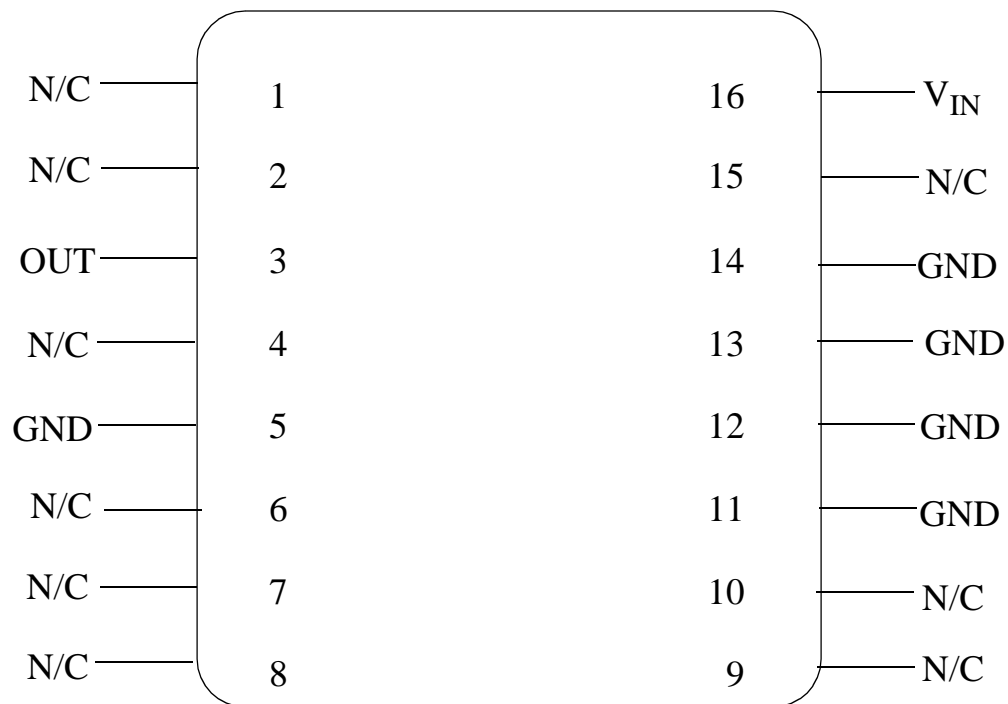
CERDIP (J) ,  
16 LEAD



**LM3940WG**  
**16 - LEAD CERAMIC SOIC**  
**CONNECTION DIAGRAM**  
**TOP VIEW**  
**P000377A**



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 2900 SEMICONDUCTOR DRIVE  
 SANTA CLARA, CA 95050



**LM3940J**  
**16 - LEAD DIP**  
**CONNECTION DIAGRAM**  
**TOP VIEW**  
**P000389A**



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 SANTA CLARA, CA 95050





**Revision History**

Rev	ECN #	Rel Date	Originator	Changes
0A0	M0002963	11/18/98	Rose Malone	Initial Release of MDS: MNLM3940-3.3-X, Rev. 0A0.
0B0	M0003105	11/18/98	Rose Malone	Update MDS: MNLM3940-3.3-X, Rev. 0A0 to MNLM3940-3.3-X, Rev. 0B0.